



Product Description

The FMS2029 is a low-loss, high-isolation, broadband, single-pole-single-throw Gallium Arsenide switch, designed on the FL05 0.5µm switch process from RFMD. It offers absorptive properties from both ports (50Ω terminations).

This process technology offers leading-edge performance optimized for switch applications.

The FMS2029 is developed for the broadband communications, instrumentation and electronic warfare markets.

Features

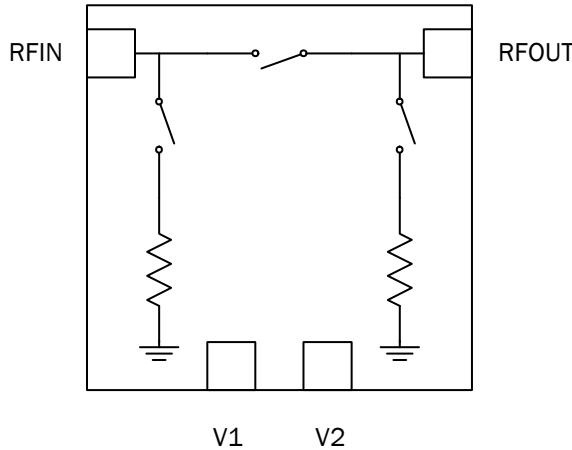
- Low Insertion Loss: 2.2dB at 20GHz
- High Isolation: 50dB at 20GHz
- Absorptive Input and Output in Off-state
- Excellent Low Control Voltage Performance
- Available in Die Form

Applications

- Broadband Communications
- Test Instrumentation
- Fiber Optics
- Electronic Warfare (ECM, ESM)

Optimum Technology Matching® Applied

- GaAs HBT
- GaAs MESFET
- InGaP HBT
- SiGe BiCMOS
- Si BiCMOS
- SiGe HBT
- GaAs pHEMT
- Si CMOS
- Si BJT
- GaN HEMT
- InP HBT
- RF MEMS
- LDMOS



Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Insertion Loss	-1	-0.85		dB	DC
	-1.35	-1		dB	5GHz
	-1.65	-1.4		dB	10GHz
	-2	-1.7		dB	15GHz
	-2.55	-2.3		dB	20GHz
Isolation		-60	-45	mA	DC to 20GHz
Input Return Loss (ON State)		-20	-17	dB	DC to 20GHz
Output Return Loss (ON State)		-20	-17	dB	DC to 20GHz
Input Return Loss (OFF State)		-12	-10	dB	DC to 20GHz
Output Return Loss (OFF State)		-12	-10	dB	DC to 20GHz
P1dB	24.5	26.7		dBm	2GHz, V _{CTRL} = 0V/-5V
	23.5	25.2		dBm	10GHz, V _{CTRL} = 0V/-5V
	20.5	22.5		dBm	20GHz, V _{CTRL} = 0V/-5V
		24		dBm	2GHz, V _{CTRL} = 0.2V/-2.4V
		22.5		dBm	10GHz, V _{CTRL} = 0.2V/-2.4V
		20		dBm	20GHz, V _{CTRL} = 0.2V/-2.4V

Notes: T_{AMBIENT} = 25 °C, V_{CTRL} = 0V/-5V. Specifications based on on-wafer measurements.

Absolute Maximum Ratings

Parameter	Rating	Unit
Maximum Input Power (P_{IN})	+27	dBm
Operating Temperature (T_{OPER})	-40 to 85	°C
Storage Temperature (T_{STOR})	-55 to 150	°C

Note: Operation of this device beyond any one of these limits may cause permanent damage.



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

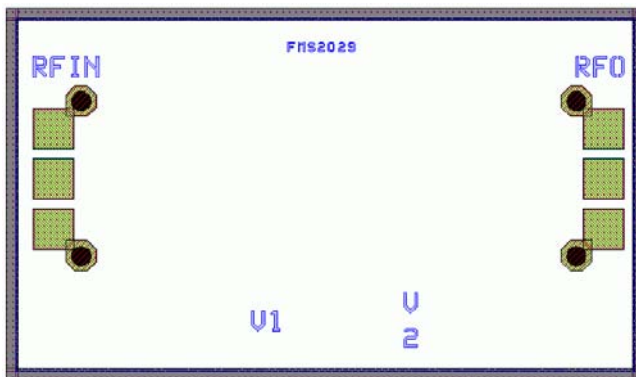
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Truth Table

Control Line		RF Path
V1	V2	RFin-RFo
High	Low	On (Low Loss)
Low	High	Off (Isolation)

High = -2.4V to -5.2V, Low = 0.2V to 1V

Pad Layout



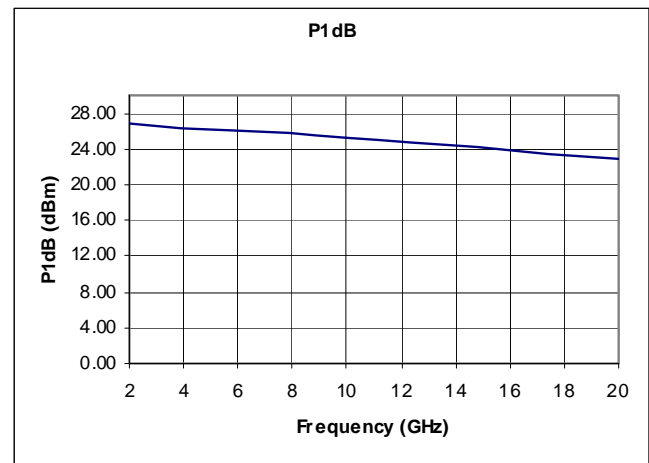
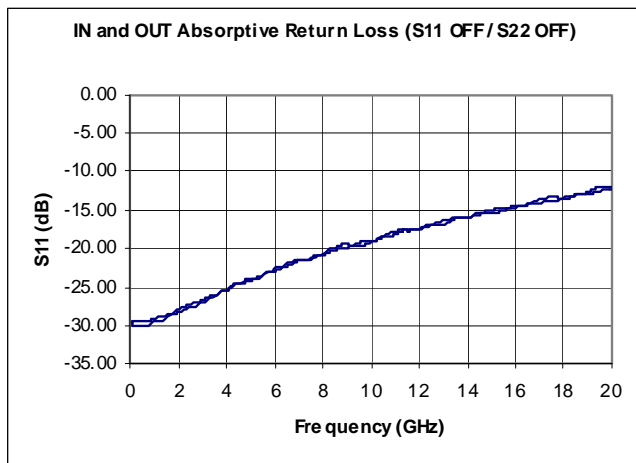
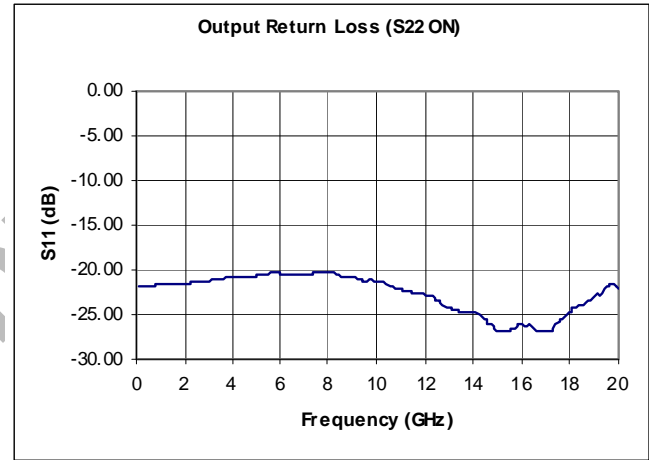
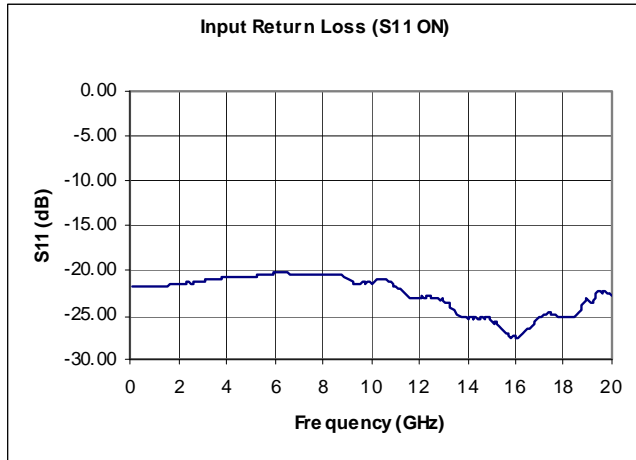
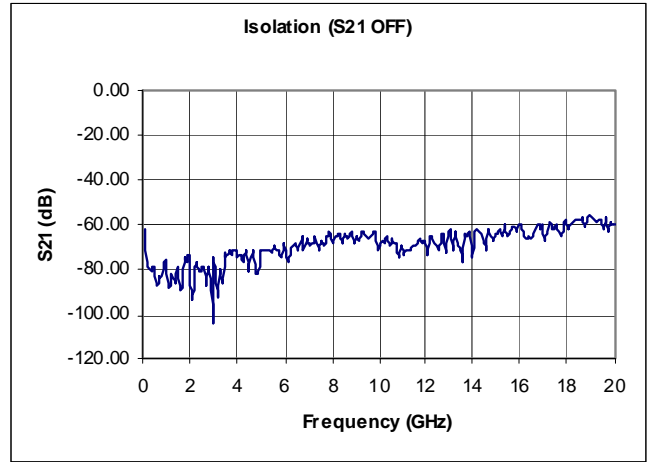
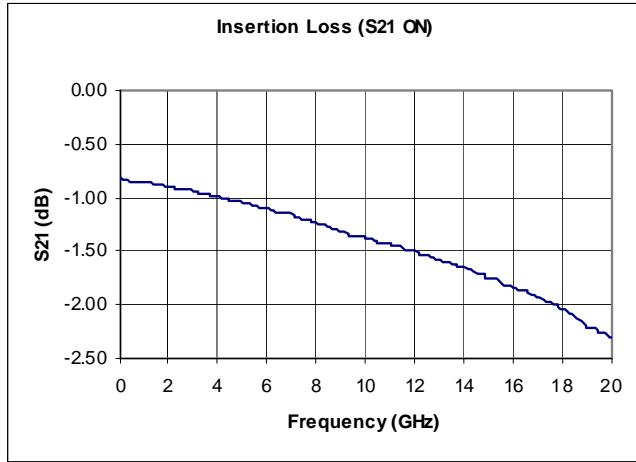
Pad	Description	Pin Coordinates (μm)
RFIN	RFIN	141, 587
RFO	R2	1789, 587
V1	R1	901, 161
V2	OUT	1101, 161

Note: Coordinates are referenced from the bottom left-hand corner of the die to the center of the bond pad opening.

Die Size (μm)	Die Thickness (μm)	Min. Bond Pad Pitch (μm)	Min. Bond Pad Opening ($\mu\text{m} \times \mu\text{m}$)
1910x1110	100	150	116x116

Typical Performance for On-Wafer Measurements

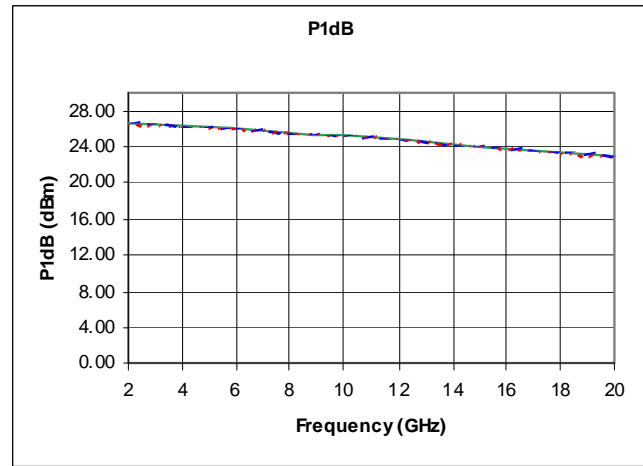
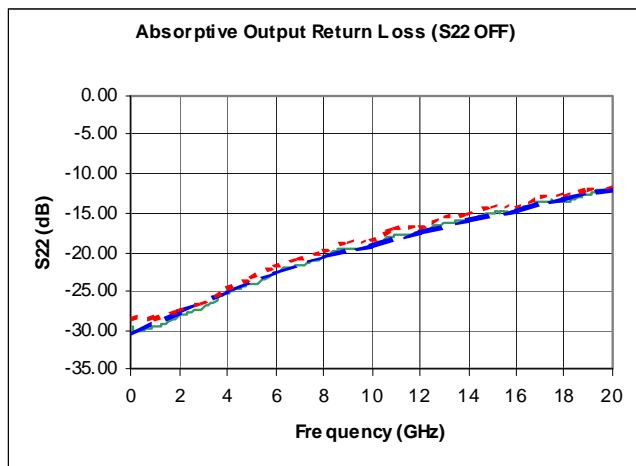
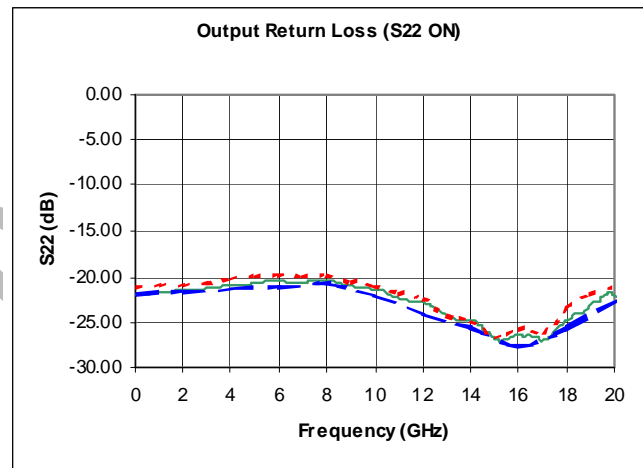
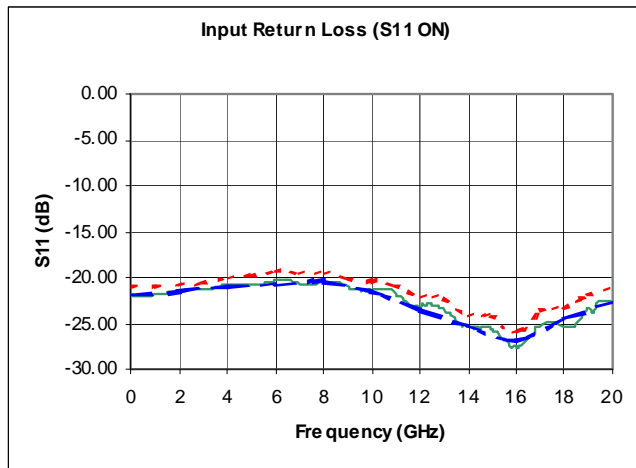
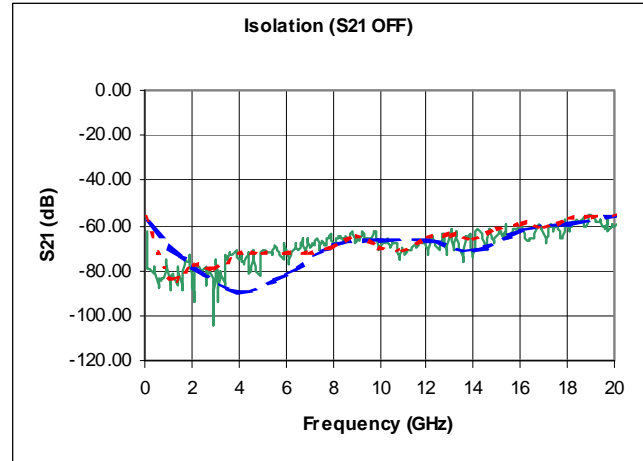
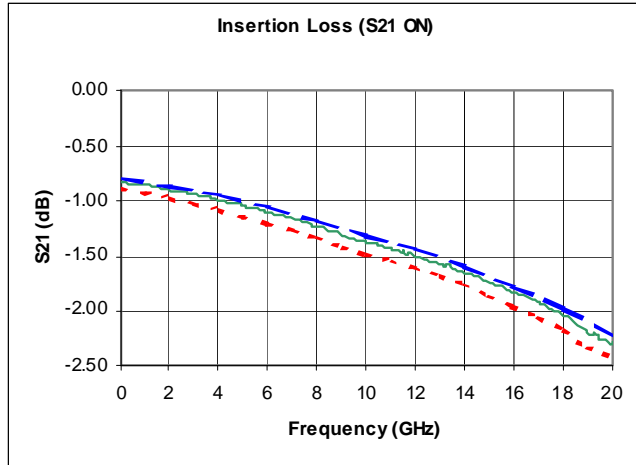
$V_{CTRL} = -5V$ (low) and $0V$ (high), $T_{AMBIENT} = 25^{\circ}C$ unless otherwise state.



Typical Performance for On-Wafer Measurements Over Temperature

$V_{CTRL} = -5V$ (low) and $0V$ (high)

— $T_{AMBIENT} = 25^{\circ}C$, - - $T_{COLD} = -40^{\circ}C$, - - - $T_{HOT} = +85^{\circ}C$



Preferred Assembly Instructions

GaAs devices are fragile and should be handled with great care. Specially designed collets should be used where possible.

The back of the die is metallized and the recommended mounting method is by the use of conductive epoxy. Epoxy should be applied to the attachment surface uniformly and sparingly to avoid encroachment of epoxy onto the top face of the die. Ideally it should not exceed half the chip height. For automated dispense Ablestick LMISR4 is recommended and for manual dispense Ablestick 84-1 LMI or 84-1 LMIT are recommended. These should be cured at a temperature of 150 °C for one hour in an oven especially set aside for epoxy curing only. If possible the curing oven should be flushed with dry nitrogen. The gold-tin (80% Au 20% Sn) eutectic die attach has a melting point of approximately 280 °C but the absolute temperature being used depends on the leadframe material used and the particular application. The maximum time at used should be kept to a minimum.

This part has gold (Au) bond pads requiring the use of gold (99.99% pure) bondwire. It is recommended that 25.4µm diameter gold wire be used. Recommended lead bond technique is thermocompression wedge bonding with 0.001” (25µm) diameter wire. Bond force, time stage temperature, and ultrasonics are all critical parameters and the settings are dependent on the setup and application being used. Ultrasonic or thermosonic bonding is not recommended.

Bonds should be made from the die first and then to the mounting substrate or package. The physical length of the bondwires should be minimized especially when making RF or ground connections.

Handling Precautions



To avoid damage to the devices, care should be exercised during handling. Proper Electrostatic Discharge (ESD) precautions should be observed at all stages of storage, handling, assembly, and testing.

ESD/MSL Rating

These devices should be treated as Class 1A (250V to 500V) using the human body model as defined in JEDEC Standard No. 22-A114. Further information on ESD control measures can be found in MIL-STD-1686 and MIL-HDBK-263. This is an unpackaged part and therefore no MSL rating applies.

Application Notes and Design Data

Application Notes and design data including S-parameters are available on request from www.rfmd.com.

Reliability

An MTF of in excess of 9 million hours at a channel temperature of 150 °C is achieved for the process used to manufacture this device.

Disclaimers

This product is not designed for use in any space-based or life-sustaining/supporting equipment.

Ordering Information

Quantity	Ordering Code
Standard order quantity (waffle pack)	FMS2029-000
Small quantity (25)	FMS2029-000SQ
Sample quantity (3)	FMS2029-000S3